

Title (en)

NANOSTRUCTURES WITH NEGATIVE DIFFERENTIAL RESISTANCE AND METHOD FOR MAKING SAME

Title (de)

NANOSTRUKTUREN MIT NEGATIVEM DIFFERENTIELLEM WIDERSTAND UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)

NANOSTRUCTURES A RESISTANCE DIFFERENTIELLE NEGATIVE ET LEUR PROCEDE DE FABRICATION

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Application

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Abstract (en)

[origin: WO2007003576A1] The invention concerns nanostructures of 0, 1, 2 and 3 dimensions, with negative differential resistance and a method for making said nanostructures. The inventive nanostructure is in particular useful in nanoelectronics. It comprises at least one structure (32) or at least a plurality of said at least one structure, on the surface of a silicon carbide substrate (30), the structure being selected among quantum connection pads, atomic segments, atomic lines and aggregates, and at least one metal deposit (34), said metal deposit covering at least the structure or at least the plurality of said at least one structure, or the combination of at least two of said structures with 0, 1, 2 or 3 dimensions.

IPC 8 full level

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